

## ZENER VOLTAGE REGULATION WITH TEMPERATURE

By Kent Walters and Mel Clark

Zener diodes are affected by temperature changes associated with their voltage temperature coefficient ( $\alpha_{VZ}$ ). This characteristic  $\alpha_{VZ}$  is usually included in the applicable zener specification data sheet where it is often stated in a percent change in zener voltage per degree centigrade ( $\%/^{\circ}\text{C}$ ), or occasionally in  $\text{mV}/^{\circ}\text{C}$ . The  $\alpha_{VZ}$  can be as low as  $-0.09\ \%/^{\circ}\text{C}$  for low voltage zeners, or as high as  $+0.110\ \%/^{\circ}\text{C}$  for high voltage zeners. This is further illustrated in Figure 1.

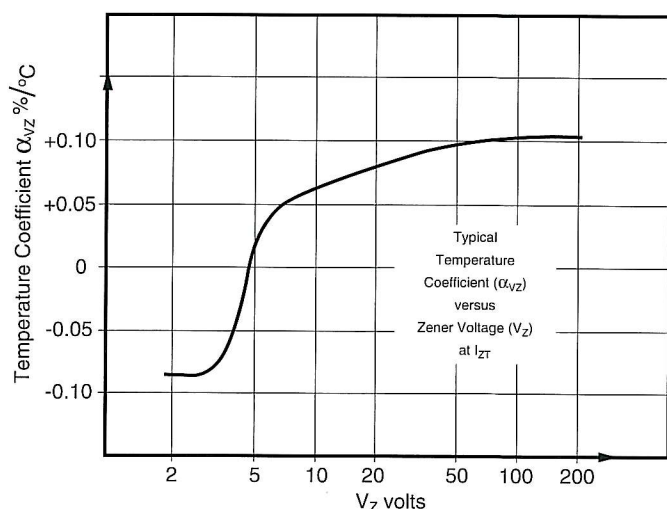


Figure 1. Temperature Coefficient vs Zener Voltage

The temperature coefficient is used in predicting voltage-temperature behavior. The zener junction temperature ( $T_J$ ) will be affected by both the ambient environment and self heating effects from applied zener power ( $P = V_Z \times I_Z$ ). Self heating is generated by zener package thermal resis-

tance from junction to case ( $R_{\theta JC}$ ) or lead ( $R_{\theta JL}$ ). This MicroNote™ will focus primarily on outside ambient temperature ( $T_A$ ) and its effects on zener voltage  $V_Z$ . Internal heating and heat sink mounting considerations will be further described in MicroNote 204.

Figure 1 shows that a negative to positive temperature coefficient “transition” will occur in the vicinity of five volts for most zener product designs. When well above five volts, the positive  $\alpha_{VZ}$  for avalanche breakdown is generally independent of operating current ( $I_Z$ ). When in the five volt zener device region or below where transition to field emission or “tunneling breakdown” occurs, negative values of  $\alpha_{VZ}$  are observed that are also notably affected by various operating current values. This phenomenon and its typical characteristics are illustrated in Figure 2 for 500 mW zeners. At very low zener voltages where field emission predominates, the  $\alpha_{VZ}$  is again unaffected by operating current. Although the  $\alpha_{VZ}$  is provided at test current ( $I_{ZT}$ ), zeners in the “transition” region will usually specify a sufficiently wide tolerance of temperature coefficient for general consideration with typical operating current variations.

Zeners are specified for voltage ( $V_Z$ ) at ambient  $T_A$  of  $25^{\circ}\text{C}$ . The voltage change ( $\Delta V_Z$ ) may be calculated for PN junction temperature change  $\Delta T_J$  from an initial  $T_A$  of  $25^{\circ}\text{C}$  using the formula:

$$\Delta V_Z = \alpha_{VZ} \times V_Z \times \Delta T_J / 100.$$

For low power levels or pulse test methods, the  $T_J$  temperature will approximate  $T_A$ . However, most zener JEDEC “1N” diode registrations are specified for  $V_Z$  at dc thermal equilibrium

(Continued)

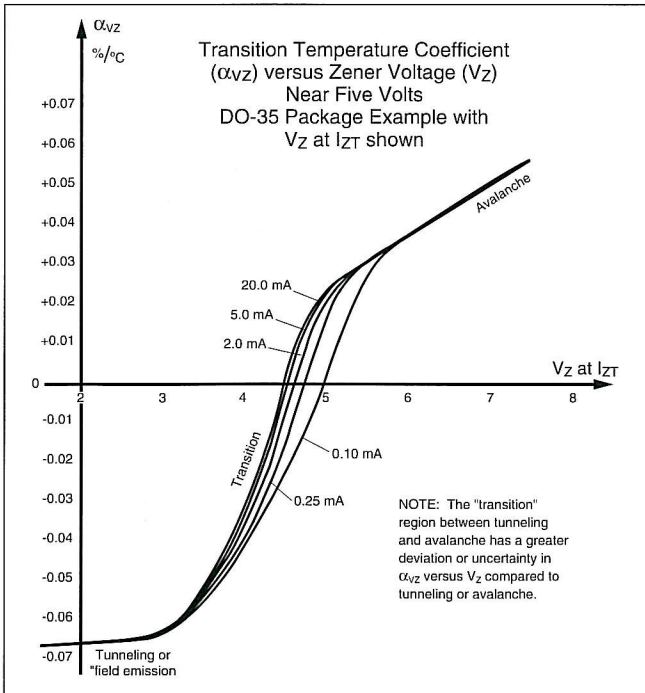


Figure 2. Transition Temperature Coefficient vs Zener Voltage Near Five Volts

conditions at their specified test current  $I_{ZT}$ . These dc power test conditions require a period of time in self heating before thermal equilibrium is achieved with internal zener junction temperature  $T_J$  above ambient  $T_A$ . A difference will then exist in zener voltage pulse testing compared to specified thermal equilibrium that often require 20 seconds or longer to achieve. The described voltage shift is easily observed for axial lead package configurations tested at 25% of full rated power, despite heatsinking at typical specified lead lengths of 0.375 inch (10 mm) from the body.

When zener thermal equilibrium conditions have already been included for  $V_Z$  reference and an external ambient temperature change of  $\Delta T_A$  causes further changes in voltage  $\Delta V_Z$ , a similar calculation applies. This can simply be expressed as:

$$\Delta V_Z = \alpha_{VZ} \times V_Z \times \Delta T_A / 100.$$

Additional important considerations to package mounting and thermal resistance on PN junction temperatures and zener voltage will be further described in MicroNote 204.

Corporate Applications Engineering Department - 602-941-6300, Ext. 433 or 524

**Microsemi Corp.**

The diode experts

## MICROSEMI CORPORATION

### Headquarters:

**Santa Ana, CA** - 2830 South Fairview Street, P.O. Box 26890, Santa Ana, CA 92799-6890, Phone: (714) 979-8220, FAX: (714) 557-5989

### Divisions:

**Scottsdale, AZ** - 8700 East Thomas Road, P.O. Box 1390, Scottsdale, AZ 85252, Phone: (602) 941-6300, FAX: (602) 947-1503

**Broomfield, CO** - 800 Hoyt Street, Broomfield, CO 80020, Phone: (303) 469-2161, FAX: (303) 466-3775

**Chatsworth, CA** - 9261 Owensmouth Avenue, Chatsworth, CA 91311, Phone: (818) 701-4933, (800) 346-3371, FAX: (818) 701-4939

**Watertown, MA** - 580 Pleasant Street, Watertown, MA 02172, Phone: (617) 926-0404, FAX: (617) 924-1235

**Sertech Labs, Inc.** - 580 Pleasant Street, Watertown, MA 02172, Phone: (617) 924-9280, FAX: (617) 924-1235

### International Sales Offices:

**Ireland** - Industrial Estate, Gort Road, Ennis, County Clare, Ireland, Phone: (065) 40044, FAX: (065) 22298

**Hong Kong** - 5/F-7/F, Meeco Ind. Building, 53-55 Au Pui Wan Street, Fotan, Shatin, N.T., Hong Kong, Phone: (852) 692-1202, FAX: (852) 691-0544